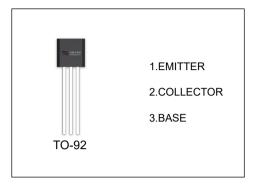


8550S TRANSISTOR (PNP)

FEATURE

Excellent h_{FE} linearity



ORDERING INFORMATION

Part Number	Package	Packing Method	Pack Quantity
8550S	TO-92	Bulk	1000pcs/Bag
8550S-TA	TO-92	Таре	2000pcs/Box

MAXIMUM RATINGS (Ta=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage	-40	V
V _{CEO}	Collector-Emitter Voltage	-25	V
V _{EBO}	Emitter-Base Voltage	-5	V
Ic	Collector Current -Continuous		mA
Pc	Collector Dissipation	625	mW
T _J ,T _{stg}	Operation Junction and Storage Temperature Range	-55-150	°C



Parameter	Symbol	Test conditions	Min	Тур	Max	Unit
Collector-base breakdown voltage	ge V _{(BR)CBO} I _C = -100uA, I _E =0		-40			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C = -1mA, I _B =0	-25			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E = -100uA, I _C =0	-5			V
Collector cut-off current	I _{CBO}	V _{CB} = -40V, I _E =0			-0.1	uA
Collector cut-off current	I _{CEO}	V _{CE} = -20V,I _B =0			-0.1	uA
Emitter cut-off current	I _{EBO}	V _{EB} = - 3V, I _C =0			-0.1	uA
DC comment soin	h _{FE(1)}	V _{CE} = -1V, I _C = -50mA	85		400	
DC current gain	h _{FE(2)}	V _{CE} = -1V, IC= -500mA	50			
Collector-emitter saturation voltage V _{CE}		I _C =-500mA, I _B =-50mA			-0.6	V
Base-emitter saturation voltage	V _{BE} (sat)	I _C =-500mA, I _B =-50mA			-1.2	V
Transition frequency	f _T	V _{CE} =- 6V, I _C =-20mA f =30MHz	150			MHz

CLASSIFICATION OF hfe(1)

_		- ' (1)				
	Rank	В	С	D	D3	
	Range	85-160	120-200	160-300	300-400	



